

PHPT61010PY

100 V, 10 A PNP high power bipolar transistor 20 March 2015

Product data sheet

1. General description

PNP high power bipolar transistor in a SOT669 (LFPAK56) Surface-Mounted Device (SMD) power plastic package.

NPN complement: PHPT61010NY.

2. Features and benefits

- High thermal power dissipation capability
- Suitable for high temperature applications up to 175 °C
- Reduced Printed-Circuit Board (PCB) requirements comparing to transistors in DPAK
- High energy efficiency due to less heat generation
- AEC-Q101 qualified

3. Applications

- Power management
- Load switch
- Linear mode voltage regulator
- Backlighting applications
- Motor drive
- Relay replacement

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-100	V
I _C	collector current		-	-	-10	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse	-	-	-20	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -10 A; I_B = -1 A; $t_p \le 300 \text{ μs}$; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	-	53	80	mΩ



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter	mb	C
2	Е	emitter		В—
3	Е	emitter	q	'*_
4	В	base	Sym132	sym132
mb	С	collector	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PHPT61010PY	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PHPT61010PY	1010PAB

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-100	V
V_{CEO}	collector-emitter voltage	open base		-	-100	V
V _{EBO}	emitter-base voltage	open collector		-	-8	V
I _C	collector current			-	-10	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-20	Α
I _B	base current			-	-1	Α
I _{BM}	peak base current	t _p ≤ 1 ms; pulsed		-	-2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	1.5	W
			[2]	-	3.7	W
			[3]	-	5	W
			[4]	-	25	W
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

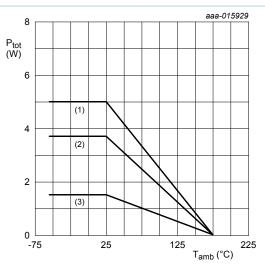
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated mounting pad for collector 6 cm².

^[3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

^[4] Power dissipation from junction to mounting base.

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- (1) Ceramic PCB, Al₂O₃, standard footprint
- (2) FR4 PCB, mounting pad for collector 6 cm²
- (3) FR4 PCB, standard footprint

Fig. 1. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance		[1]	-	-	100	K/W
	from junction to ambient		<u>[2]</u>	-	-	41	K/W
	ambient		[3]	-	-	30	K/W
R _{th(j-mb)}	thermal resistance from junction to mounting base			-	-	6	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [3] Device mounted on an ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.

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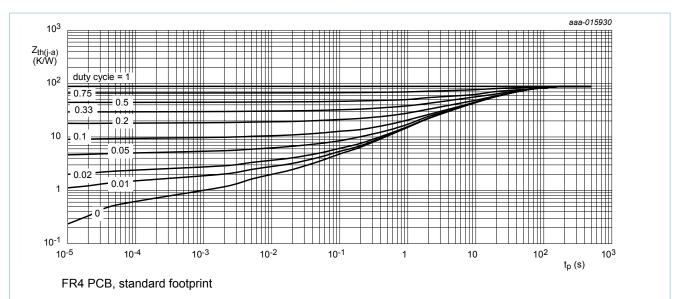


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

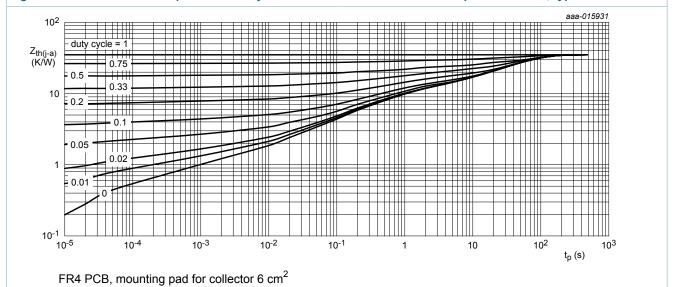


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

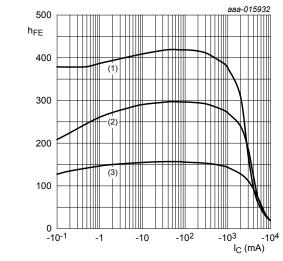
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{СВО}	collector-base cut-off	V_{CB} = -80 V; I_{E} = 0 A; T_{amb} = 25 °C	-	-	-100	nA
	current	$V_{CB} = -80 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -80 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
I _{ЕВО}	emitter-base cut-off current	V_{EB} = -8 V; I_{C} = 0 A; T_{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -0.5 A; T_{amb} = 25 °C	180	330	-	
		V_{CE} = -2 V; I_{C} = -1 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	170	265	-	
		V_{CE} = -2 V; I_{C} = -5 A; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C; pulsed	60	75	-	
		V_{CE} = -2 V; I_{C} = -10 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	10	15	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; t_{p} ≤ 300 µs; δ ≤ 0.02; T_{amb} = 25 °C	-	-55	-90	mV
		I_{C} = -5 A; I_{B} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	-	-160	-250	mV
		I_C = -10 A; I_B = -1 A; pulsed; $t_p \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	-	-530	-800	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -10 A; I_B = -1 A; $t_p \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C; pulsed	-	53	80	mΩ
V _{BEsat}	base-emitter saturation voltage	I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	-	-	-0.9	V
		I_{C} = -5 A; I_{B} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-1.1	V
		I_{C} = -10 A; I_{B} = -1 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	-1.3	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -0.5 A; T_{amb} = 25 °C	-	-	-0.8	V
d	delay time	$V_{CC} = -12.5 \text{ V}; I_C = -5 \text{ A};$	-	20	-	ns
t _r	rise time	$I_{Bon} = -250 \text{ mA}; I_{Boff} = 250 \text{ mA};$	-	145	-	ns
ton	turn-on time	T _{amb} = 25 °C	-	165	-	ns
s	storage time		-	155	-	ns
t _f	fall time		-	80	-	ns
t _{off}	turn-off time		-	235	-	ns

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f _T	transition frequency	V _{CE} = -10 V; I _C = -500 mA; f = 100 MHz; T _{amb} = 25 °C	-	90	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	101	-	pF



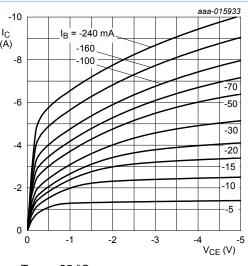
 $V_{CE} = -2 V$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) T_{amb} = 25 °C

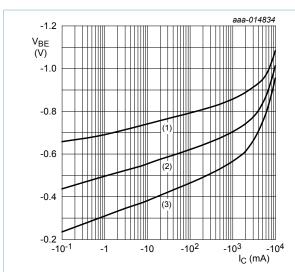
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



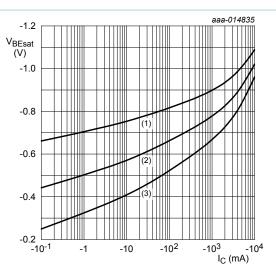
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb}$$
 = 100 °C

Fig. 6. Base-emitter voltage as a function of collector current; typical values



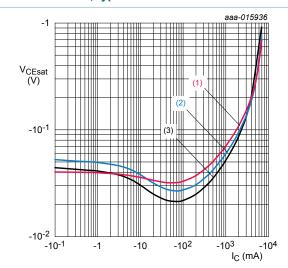
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values



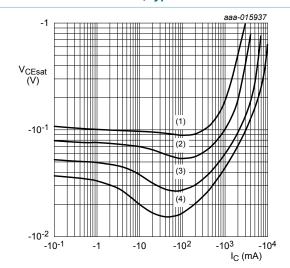
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values



(1)
$$I_C/I_B = 100$$

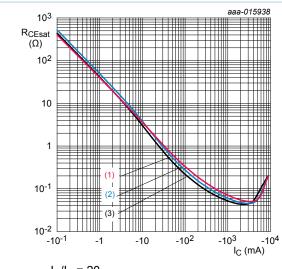
(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 20$$

$$(4) I_C/I_B = 10$$

Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

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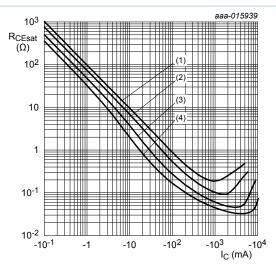
 $I_{\rm C}/I_{\rm B} = 20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

 $(3) T_{amb} = -55 °C$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values



 T_{amb} = 25 °C

(1) $I_C/I_B = 100$

(2) $I_C/I_B = 50$

(3) $I_C/I_B = 20$

(4) $I_{\rm C}/I_{\rm B} = 10$

Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

11. Test information

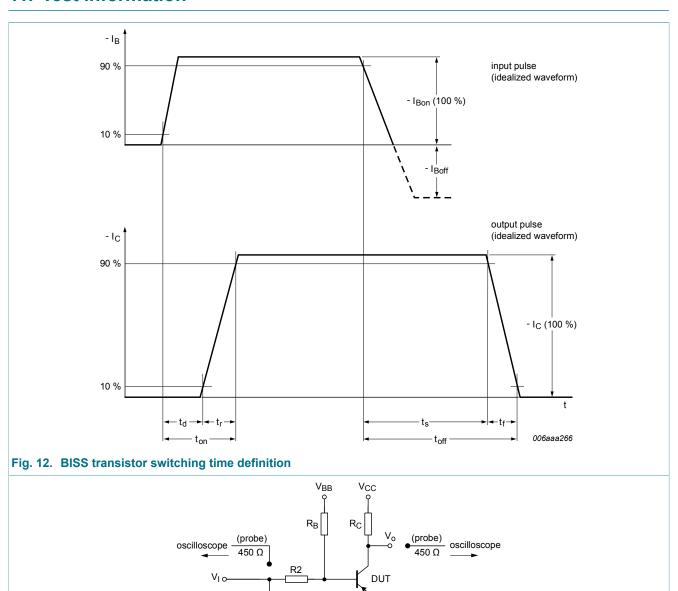


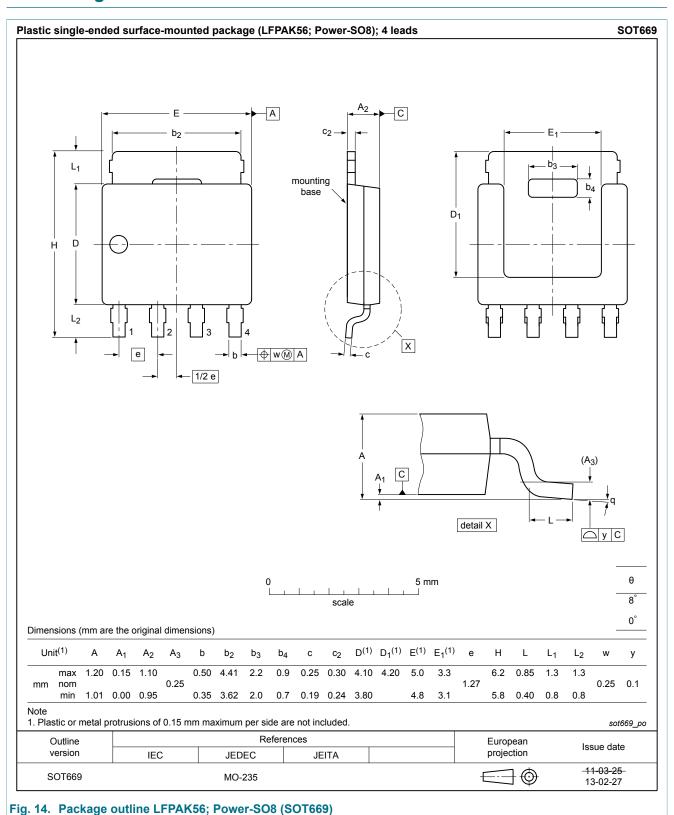
Fig. 13. Test circuit for switching times

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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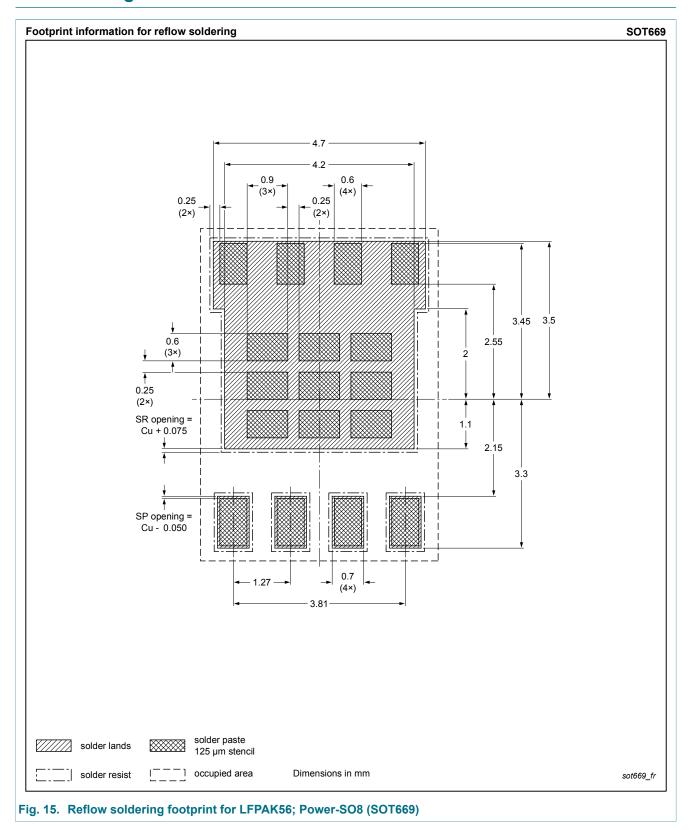
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PHPT61010PY v.1	20150320	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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